Products | Applications | Design Support | Ordering | Company

Microsemi.

Power Matters[™]

Home ▶ 2N1209 (#22951)

2N1209 (#22951)

Products

- ▶ Product Directory
- ► Applications Directory
- ▶ Parametric Search

Overview Diagrams

Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			5.00	V
DC Current Gain	HFE	20.00		80.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			45.00	V
Collector Current (dc)	I _C			5.00	А
Collector-Emitter Voltage (Base Open)	V_{CEO}			45.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			5.00	V
Power Dissipation, Total	P _T			85.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ NPN Transistor

Related Links

Technical support
Sales Contacts
Available Stock
Sales Contacts
RFQ/Samples

Products | Applications | Design Support | Company | Careers | Investors | Survey | Privacy Policy | Terms & Conditions | Product Disclaimer Copyright © 2015 Microsemi Corporation. All rights reserved. The Microsemi logo is a registered trademark of Microsemi Corporation.